AG 3A ... AG 3M

Silicon Rectifier Cells

with polysiloxan passivation

AG 3A ... AG3M

Forward Current: 3 A

Reverse Voltage: 50 to 1000 V

Publish Data

Features

Mechanical Data

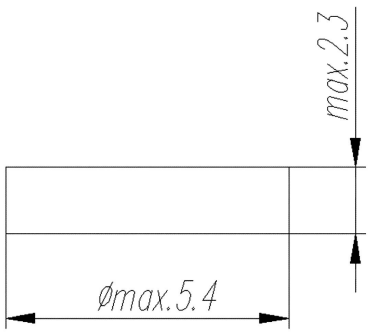
- Weight approx. 0.3g
- 2) I_F = 3A, Tj = 25ºC

Type	Repetitive peak reverse voltage V_{RRM} V	Surge peak reverse voltage V_{RSM} V	Max. reverse recovery time I_F = A, I_R = A, I_{RR} = A, t_{rr} ns	Max. forward voltage V_F 2)
AG 3A	50	80	/	<1,2
AG 3B	100	130	/	<1,2
AG 3D	200	250	/	<1,2
AG 3G	400	450	/	<1,2
AG 3J	600	700	/	<1,2
AG 3K	800	1000	/	<1,2
AG 3M	1000	1300	/	<1,2

Absolute Maximum Ratings		T_c = 25ºC unless otherwise specified	
Symbol	**Conditions**	**Values**	**Units**
I_{FAV}	Max. averaged fwd. current, R-load, T_A = 100 °C 1)	3	A
I_{FRM}	Repetitive peak forward current f > 15 Hz 1)	30	A
I_{FSM}	Peak forward surge current 50 Hz half sinus-wave 3)	150	A
i²t	Rating for fusing, t < 10 ms 3)	110	A²s
R_{thA}	Max. thermal resistance junction to ambient 1)		K/W
R_{thT}	Max. thermal resistance junction to terminals 1)		K/W
T_j	Operating junction temperature	-50 ... +150ºC	°C
T_s	Storage temperature	-50 ... +150ºC	°C

Characteristics		T_c = 25ºC unless otherwise specified	
Symbol	**Conditions**	**Values**	**Units**
I_R	Maximum leakage current, T_j = 25 °C; V_R = V_{RRM}	10	µA
	T_j = 100 °C; V_R = V_{RRM}	1	mA
C_J	Typical junction capacitance (at MHz and applied reverse voltage of V)		pF
Q_{rr}	Reverse recovery charge (U_R = V; I_F = A; dI_F/dt = A/ms)		µC
E_{RSM}	Non repetitive peak reverse avalanche energy (I_R = mA; T_j = °C; inductive load switched off)		mJ

Dimensions in mm



 © by SEMIKRON

 © by SEMIKRON